NIKO-SEM

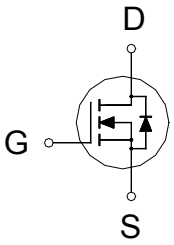
N-Channel Enhancement Mode Field Effect Transistor

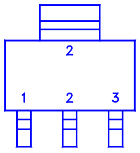
P1503BLH
SOT-223
Halogen-Free & Lead-Free

RoHS Compliant

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	15mΩ	12A





1. GATE
2. DRAIN
3. SOURCE

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A = 25 °C	I_D	12	A
	T_A = 100 °C		9.9	
Pulsed Drain Current[1]		I_{DM}	40	
Avalanche Current		I_{AS}	19	
Avalanche Energy	L = 0.1mH	E_{AS}	18	mJ
Power Dissipation[3]	T_A = 25 °C	P_D	3.9	W
	T_A = 100 °C		2.5	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	t ≦10s	$R_{\theta JA}$		32	°C / W
Junction-to-Ambient[2]	Steady-State	$R_{\theta JA}$		60	

[1]Pulse width limited by maximum junction temperature.
[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
[3]The Power dissipation is based on $R_{\theta JA}$ t ≦10s value.

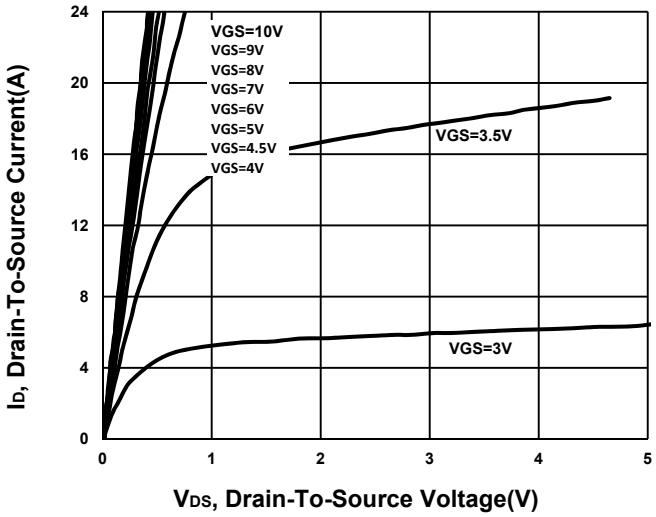
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS MIN	LIMITS TYP	LIMITS MAX	UNIT
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	1.5	3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V			1	μA
		V_{DS} = 20V, V_{GS} = 0V, T_J = 125 °C			10	

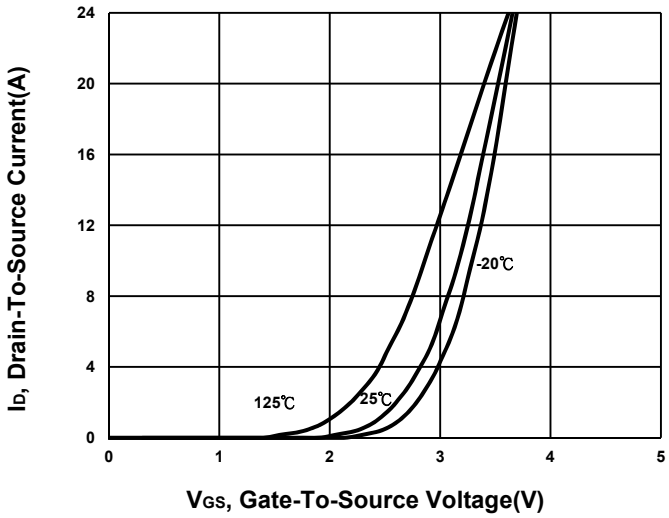
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 11A		17.5	24	mΩ
		V_{GS} = 10V, I_D = 11A		12.5	15	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 11A		20		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		935		pF
Output Capacitance	C_{oss}			147		
Reverse Transfer Capacitance	C_{rss}			106		
Gate Resistance	Rg	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		1		Ω
Total Gate Charge[2]	$Q_{g(VGS=10V)}$	V_{DS} = 15V, I_D = 11A		20		nC
	$Q_{g(VGS=4.5V)}$			11		
Gate-Source Charge[2]	Q_{gs}			3		
Gate-Drain Charge[2]	Q_{gd}			5		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 15V $I_D \cong$ 11A, V_{GS} = 10V, R_{GS} = 6Ω		20		nS
Rise Time[2]	t_r			11		
Turn-Off Delay Time[2]	$t_{d(off)}$			36		
Fall Time[2]	t_f			11		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				3.5	A
Forward Voltage[1]	V_{SD}	I_F = 11A, V_{GS} = 0V			1.1	V
Reverse Recovery Time	t_{rr}	I_F = 11A, dI/dt = 100 A/μs		15		nS
Reverse Recovery Charge	Q_{rr}			5		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

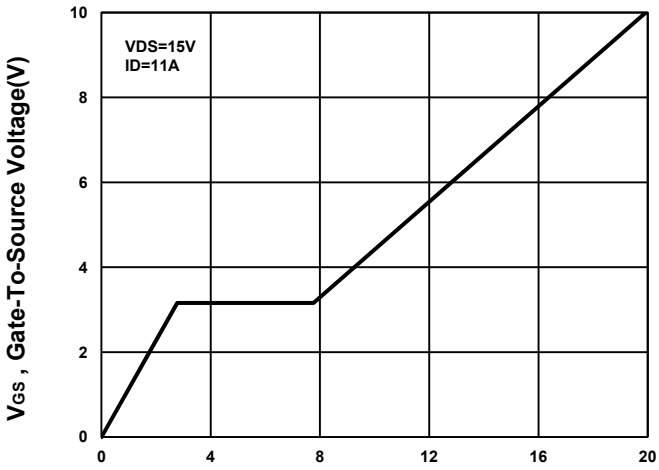
Output Characteristics



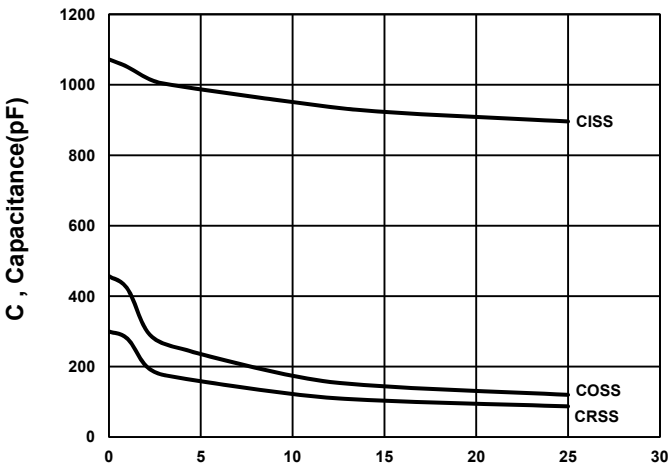
Transfer Characteristics



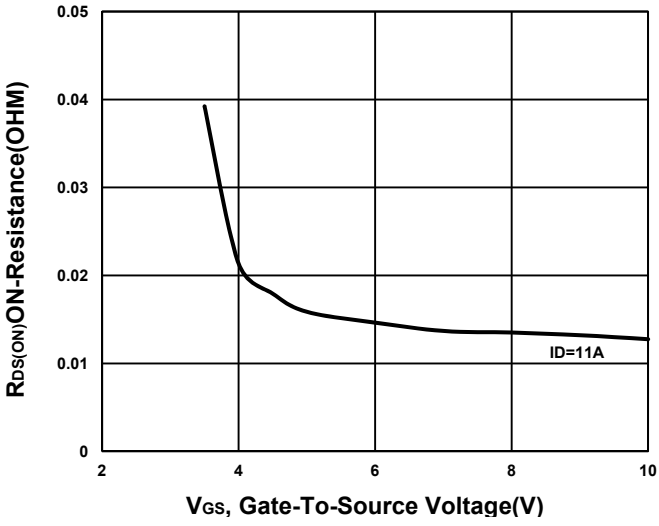
Gate charge Characteristics



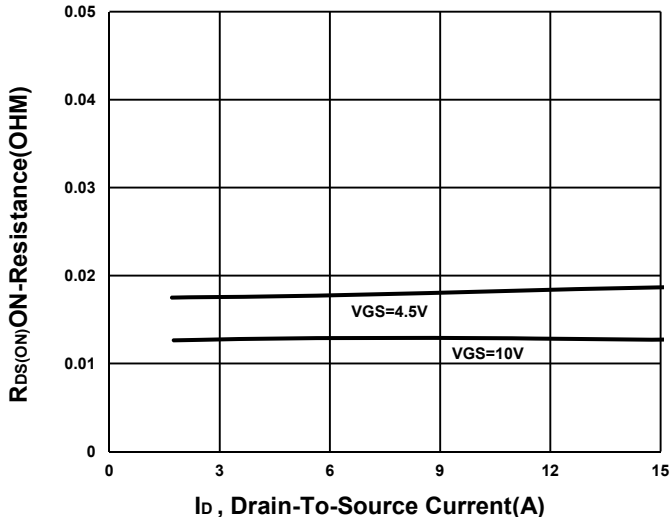
Capacitance Characteristic



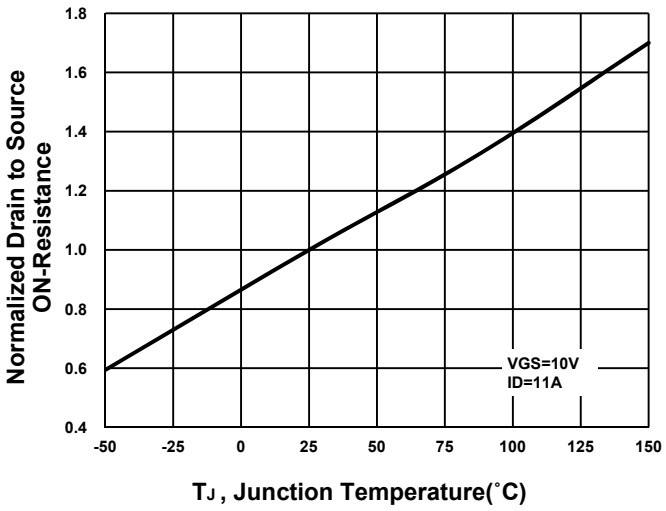
On-Resistance VS Gate-To-Source



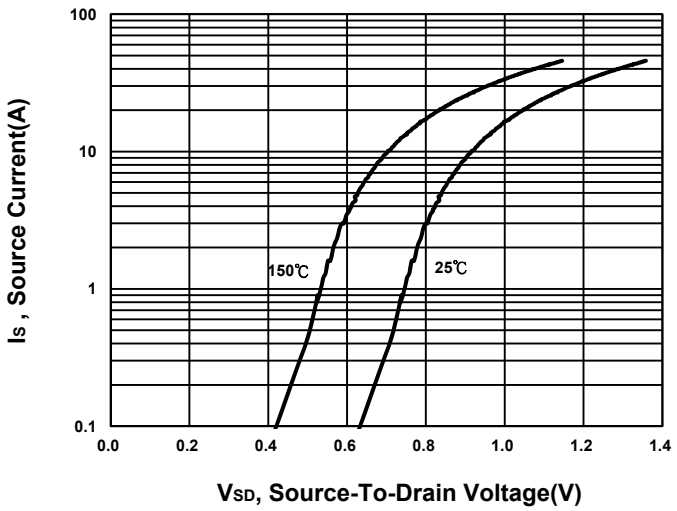
On-Resistance VS Drain Current



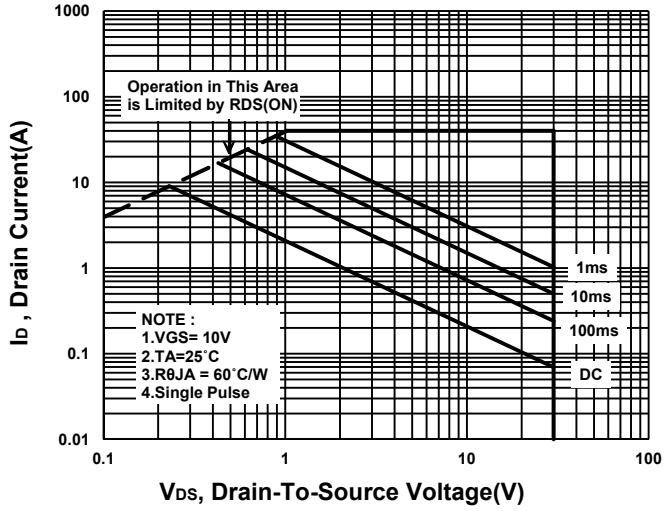
On-Resistance VS Temperature



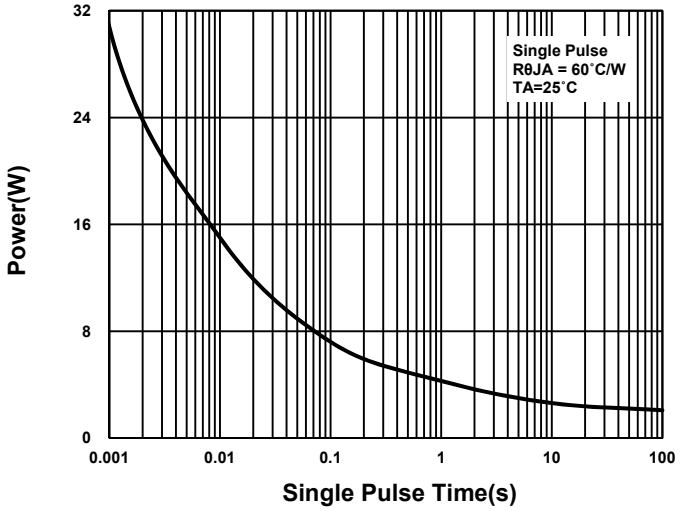
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve